

AMENDMENTS TO DRAWINGS:

The attached sheets of drawings include amendments to Figs. 4, 7-11 and 14-17.

Marked copies of amended Figs. 4, 7-11 and 14-17 are also enclosed.

HAYES SOLOWAY P.C.
3450 E. SUNRISE DRIVE,
SUITE 140
TUCSON, AZ 85718
TEL. 520.882.7623
FAX. 520.882.7643

175 CANAL STREET
MANCHESTER, NH 03101
TEL. 603.668.1400
FAX. 603.668.8567

REMARKS

The Specification has been amended to correct minor clerical errors and to better conform to the drawings.

The claims have been amended to address the 112 rejection and to clarify the invention.

The drawings have been amended to conform with US practice and to conform to the Specification.

An Abstract has been added in accordance with US practice.

No new matter has been added by any of the foregoing amendments.

Turning to the several art rejections, it is noted that all of the rejections are based in whole or in part on the '326 published application to Roche et al. The Roche et al. application based on a US application filed July 12, 2002. The instant application is a 371 of PCT/JP03/01079 which claims priority from Japanese application 2002-086196 filed March 26, 2002. Accompanying this Amendment is a certified copy of Applicants' underlying Japanese priority application, together with a verified English translation thereof. With the perfection of Applicants' priority claim, the Roche et al. published application is removed as citable prior art. Accordingly, since all of the art rejections are based in whole or in part on Roche et al., and Roche et al. has been removed as citable prior art, specific discussion of the art rejections is believed not necessary.

Having dealt with all the rejections raised by the Examiner, the application is believed to be in order for allowance. Early and favorable action are respectfully requested.

HAYES SOLOWAY P.C.
3450 E. SUNRISE DRIVE,
SUITE 140
TUCSON, AZ 85718
TEL: 520.882.7623
FAX: 520.882.7643

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MANCHESTER, NH 03101
TEL: 603.668.1400
FAX: 603.668.8567

In the event there are any fee deficiencies or additional fees are payable, please charge them (or credit any overpayment) to our Deposit Account Number 08-1391/

Respectfully submitted,



Norman P. Soloway
Attorney for Applicants
Reg. No. 24,315

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on December 21, 2006, at Tucson, Arizona.

By 

NPS:ps

HAYES SOLOWAY P.C.
3450 E. SUNRISE DRIVE,
SUITE 140
TUCSON, AZ 85718
TEL. 520.682.7623
FAX. 520.682.7643

175 CANAL STREET
MANCHESTER, NH 03101
TEL. 603.668.1400
FAX. 603.668.8567

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Annotated Marked-up Drawing Figures 4, 7-11 and 14-17



F-18-4

Fig. 4 (a) INPUT

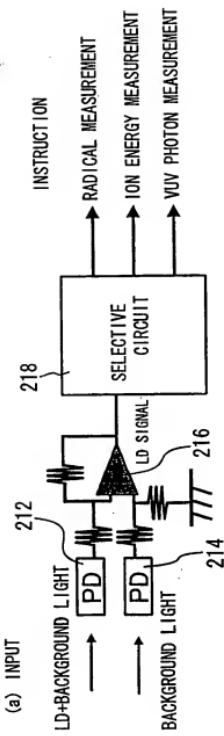


Fig. 4 (b) OUTPUT
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~~Fig. 7~~

STRUCTURE OF ON-WAFER ION ENERGY ANALYZER

Fig. 7 (a)

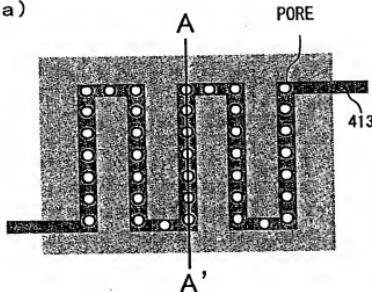


Fig. 7 (b)

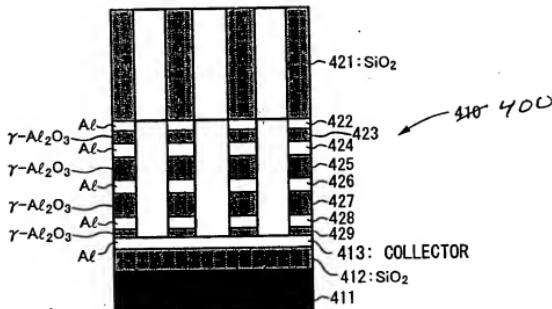


Fig. 8 MEASUREMENT SYSTEM OF ON-WAFER ION ENERGY ANALYZER

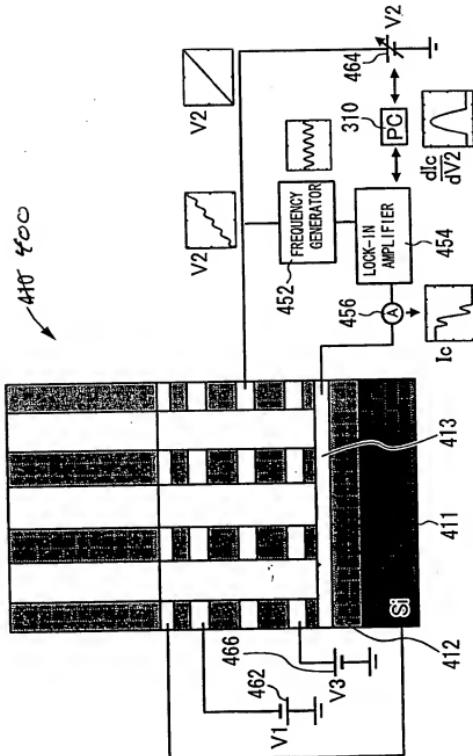


Fig. 9

Fig. 9 (a)

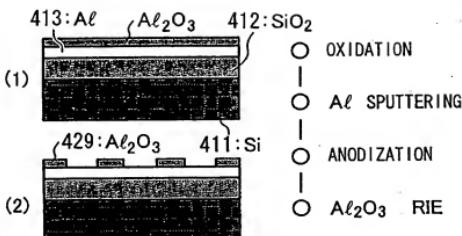


Fig. 9 (b)

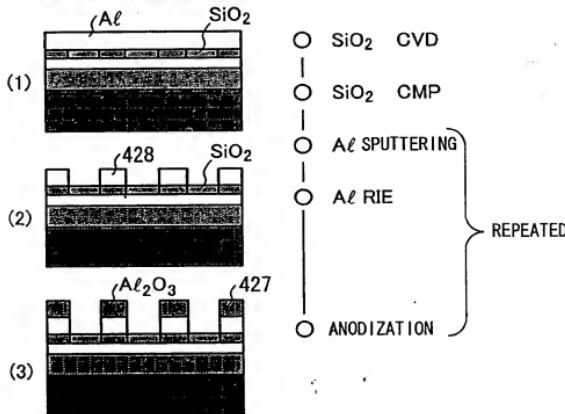


Fig. 9 (c)

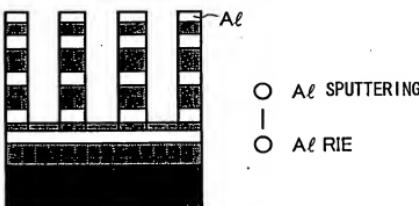


Fig. 10

Fig. 10 (d)

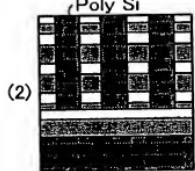
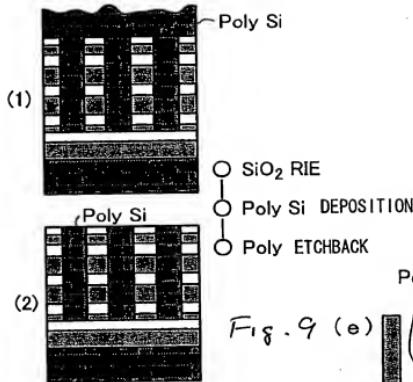


Fig. 9 (e)

○ SiO₂
DEPOSITION
○ SiO₂ RIE

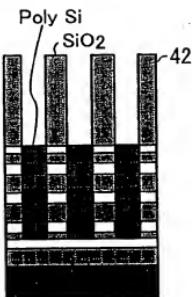


Fig. 9 (f)

○ Poly RIE

413
412
411



Fig. 1-1

Fig. 11 (a)

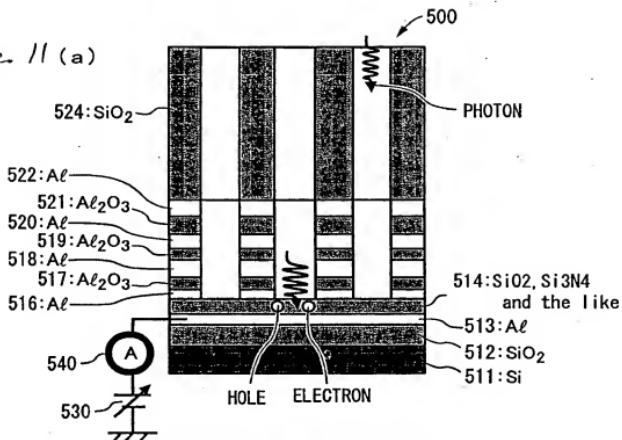


Fig. 11 (b)

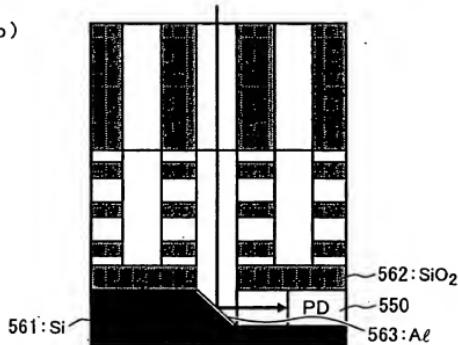


Fig. 14

Fig. 14 (a)

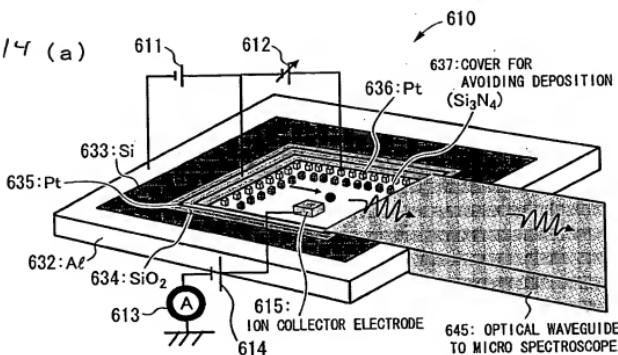


Fig. 14 (b)

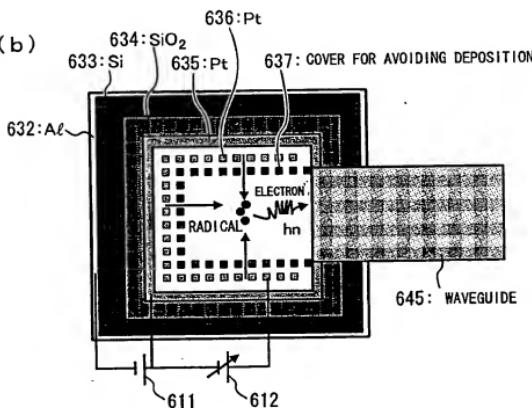


Fig. 15

MICRO SPECTROSCOPE

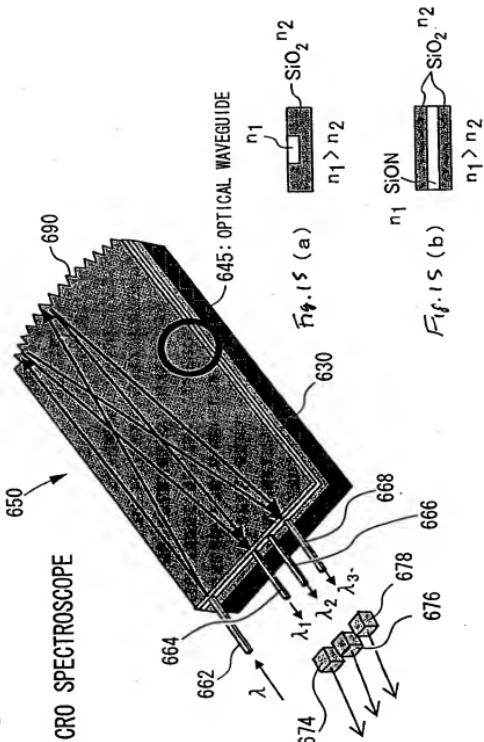


Fig. 16

MANUFACTURING PROCESS OF MICRO ION RADICAL ANALYZER(1)

Fig. 16 (a) OXIDATION



Fig. 16 (b) Si DEPOSITION, ETCHING



Fig. 16 (c) Al VAPOR DEPOSITION, ETCHING



Fig. 16 (d) SiO2 DEPOSITION, ETCHING



Fig. 16 (e) Pt DEPOSITION, PATTERNING

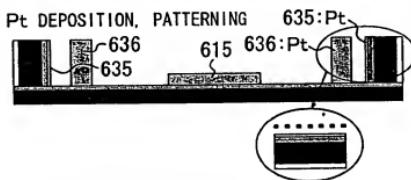


Fig. 16 (f) Si3N4 DEPOSITION, ETCHING

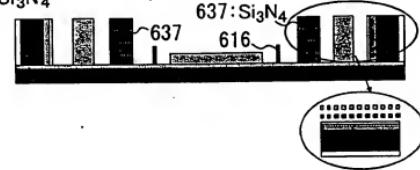


Fig. 17

MANUFACTURING PROCESS OF MICRO ION RADICAL ANALYZER(2)

Fig. 17 (g) SiO₂ DEPOSITION, ETCHING

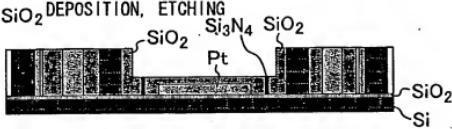


Fig. 17 (h) Si₃N₄ DEPOSITION, ETCHING

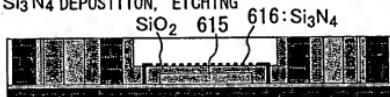


Fig. 17 (i) SiO₂ DEPOSITION, ETCHING
FORMATION OF WAVEGUIDE

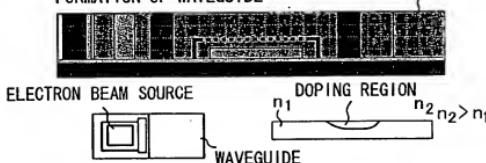


Fig. 17 (j) Si₃N₄, Si DEPOSITION

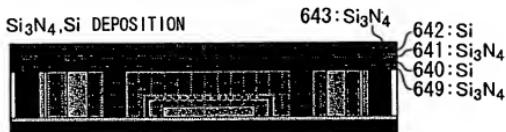


Fig. 17 (k) Si₃N₄, Si ETCHING
SiO₂ SACRIFICE LAYER ETCHING



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Replacement Drawing Figures 4, 7-11 and 14-17